

# 30A, 45V - 150V Schottky Barrier Rectifier

#### **FEATURES**

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

#### **MECHANICAL DATA**

• Case: TO-220AB

Molding compound meets UL 94V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

 Mounting torque: 0.56 N⋅m maximum • Meet JESD 201 class 1A whisker test

· Polarity: As marked

• Weight: 1.90g (approximately)

KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
I <sub>F</sub>	30	Α		
$V_{RRM}$	45 - 150	V		
I <sub>FSM</sub>	200	Α		
T <sub>J MAX</sub>	150 °C			
Package	TO-220AB			
Configuration	Dual dies			

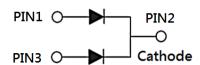








**TO-220AB** 



		MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	3045 CT-Y	3060 CT-Y	3080 CT-Y	30100 CT-Y	30150 CT-Y	UNIT
Marking code on the device		MBR 3045CT	MBR 3060CT	MBR 3080CT	MBR 30100CT	MBR 30150CT	
Repetitive peak reverse voltage	$V_{RRM}$	45	60	80	100	150	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	31	42	56	70	105	V
Forward current	I <sub>F</sub>	30			Α		
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	200				Α	
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1 0.5			Α		
Peak repetitive forward current (Rated V <sub>R</sub> , Square wave, 20KHz)	I <sub>FRM</sub>	30			Α		
Critical rate of rise of off-state voltage	dv/dt	10,000			V/µs		
Junction temperature	TJ	-55 to +150			°C		
Storage temperature	T <sub>STG</sub>	-55 to +150			°C		

#### Notes:

1.  $tp = 2.0\mu s$ , 1.0KHz

THERMAL PERFORMANCE						
PARAMETER		SYMBOL	TYP	UNIT		
Junction-to-case thermal resistance	MBR3045CT-Y MBR3060CT-Y MBR3080CT-Y	R <sub>eJC</sub>	1.0	°C/W		
Junction-to-case thermal resistance	MBR30100CT-Y MBR30150CT-Y	$R_{\Theta JC}$	1.5	°C/W		

PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
	MBR3045CT-Y	I <sub>F</sub> = 15A, T <sub>J</sub> = 25°C		-	0.70	V
	MBR3060CT-Y			-	0.77	V
	MBR3080CT-Y MBR30100CT-Y			-	0.84	V
	MBR30150CT-Y			-	0.95	V
	MBR3045CT-Y			-	0.82	V
	MBR3060CT-Y			-	-	V
	MBR3080CT-Y MBR30100CT-Y	I <sub>F</sub> = 30A, T <sub>J</sub> = 25°C		-	0.94	V
Forward voltage per	MBR30150CT-Y		.,	-	1.02	V
diode <sup>(1)</sup>	MBR3045CT-Y	I <sub>F</sub> = 15A, T <sub>J</sub> = 125°C	$V_F$	-	0.60	V
	MBR3060CT-Y			-	0.67	V
	MBR3080CT-Y MBR30100CT-Y			-	0.70	V
	MBR30150CT-Y			-	0.92	V
	MBR3045CT-Y	I <sub>F</sub> = 30A, T <sub>J</sub> = 125°C		-	0.73	V
	MBR3060CT-Y			-	-	V
	MBR3080CT-Y MBR30100CT-Y			-	0.82	V
	MBR30150CT-Y			-	0.98	V
Reverse current @ rated V <sub>R</sub> per diode <sup>(2)</sup>	MBR3045CT-Y MBR3060CT-Y MBR3080CT-Y MBR30100CT-Y	T <sub>J</sub> = 25°C		-	200	μΑ
	MBR30150CT-Y			-	100	μΑ
	MBR3045CT-Y	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	40	mA
	MBR3060CT-Y			-	10	mA
	MBR3080CT-Y MBR30100CT-Y			-	7.5	mA
	MBR30150CT-Y			-	5	mA

### Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE <sup>(1)</sup>	PACKAGE	PACKING		
MBR30xCT-Y	TO-220AB	50 / Tube		

### Notes:

1. "x" defines voltage from 45V(MBR3045CT-Y) to 150V(MBR30150CT-Y)

Fig.2 Typical Junction Capacitance



### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

**Fig.1 Forward Current Derating Curve** 

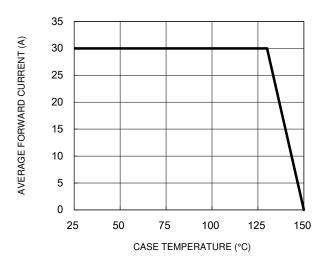


Fig.3 Typical Reverse Characteristics

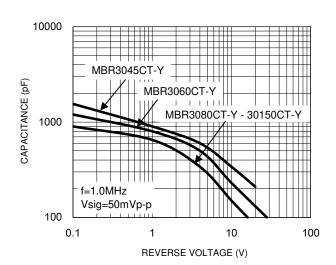
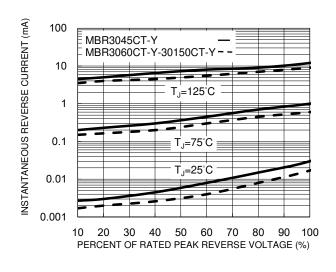


Fig.4 Typical Forward Characteristics



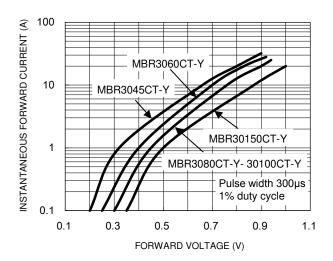
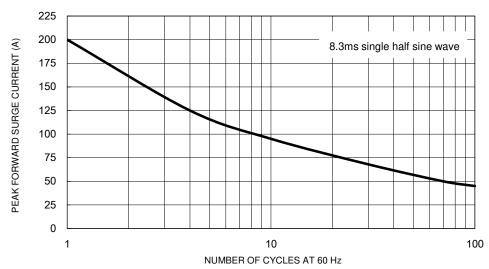


Fig.5 Maximum Non-Repetitive Forward Surge Current

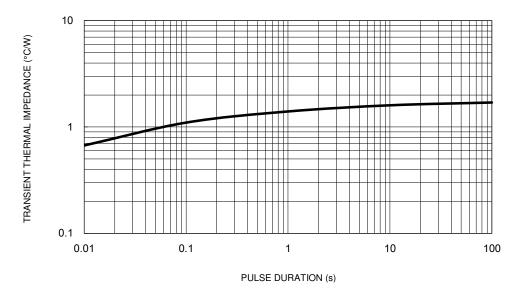


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## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

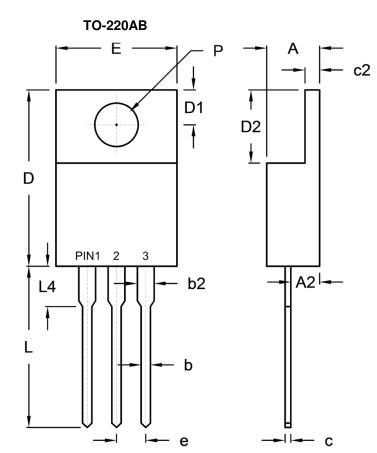
Fig.6 Typical Transient Thermal Impedance





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## **PACKAGE OUTLINE DIMENSIONS**



DIM.	Unit	(mm)	Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
Α	4.42	4.76	0.174	0.187	
A2	2.20	2.80	0.087	0.110	
b	0.68	0.94	0.027	0.037	
b2	1.14	1.77	0.045	0.070	
С	0.35	0.64	0.014	0.025	
c2	1.14	1.40	0.045	0.055	
D	14.60	16.00	0.575	0.630	
D1	2.62	3.44	0.103	0.135	
D2	5.84	6.86	0.230	0.270	
E	-	10.50	-	0.413	
е	2.41	2.67	0.095	0.105	
L	13.19	14.79	0.519	0.582	
L4	2.80	4.20	0.110	0.165	
Р	3.54	4.00	0.139	0.157	

### **MARKING DIAGRAM**



P/N = Marking Code G = Green Compound

YWW = Date Code F = Factory Code



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